

Highly Efficient Neuromorphic Computing Systems with Emerging Nonvolatile Memories

Bonan Yan

Dept. Electrical & Computer Engineering

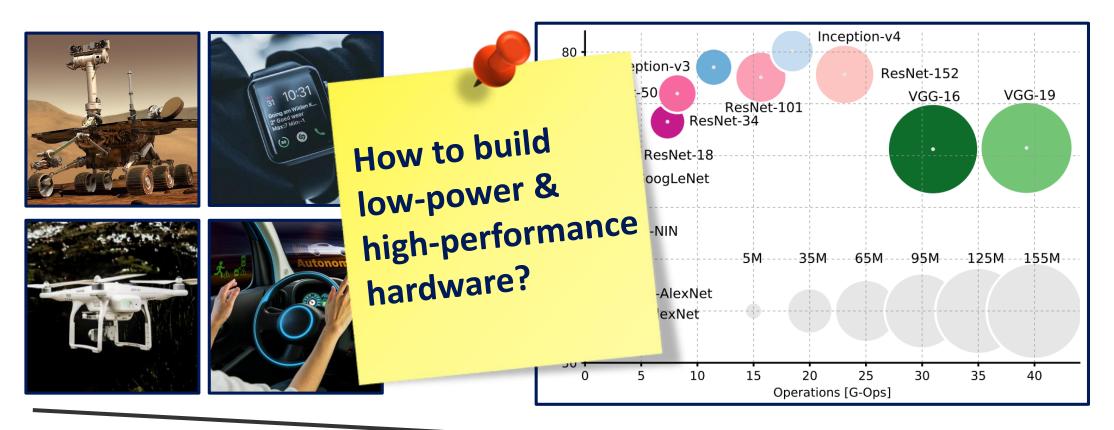
Duke University

Slides available at: https://bonanyan.github.io/bn/

Efficiency Is The Key to Ubiquitous Al

Limited Power/Energy

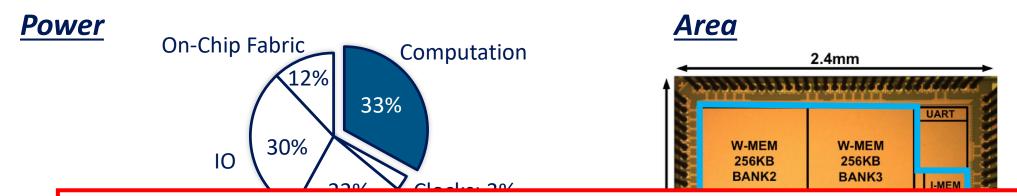
Better Accuracy Comes From Larger Models





2

Overhead Dominated by Memories



- Memory is the Bottleneck; Data Movement Is Expensive
- How to overcome the memory bottleneck?

Float ADD Register File	0.9 1	GPIO GPIO
Int Multiply Float Multiply	3.1 3.7	: Function Unit
SRAM Cache DRAM Memory	5 640	: On-chip Memory : Control Module



En

Source: AMD, Intel, [Whatmough, ISSCC 2017]

Specialized Hardware Enhances Efficiency

 $P = \alpha C V_{DD}^2 f$

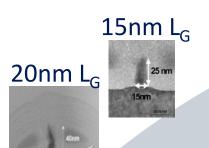
P: Power Dissipation

 α : Activity Factor

C: Load Capacitance

 V_{DD} : Power Supply

f : Clock Frequency



Multicore to Manycore





Domain-Specific





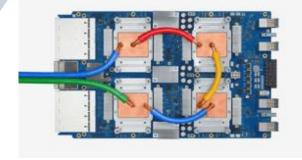






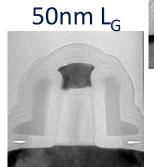




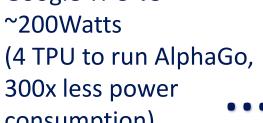


Google TPU v3 consumption)

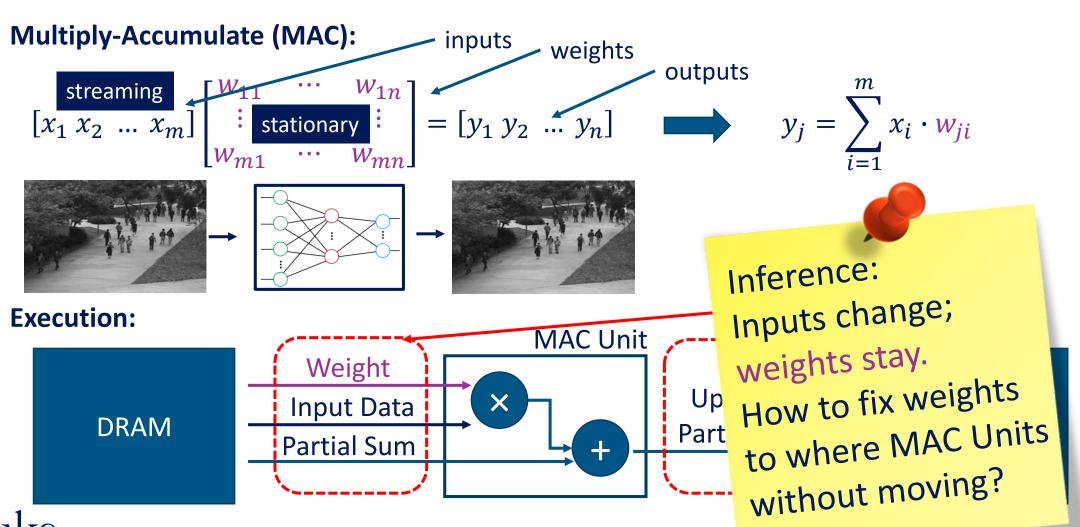




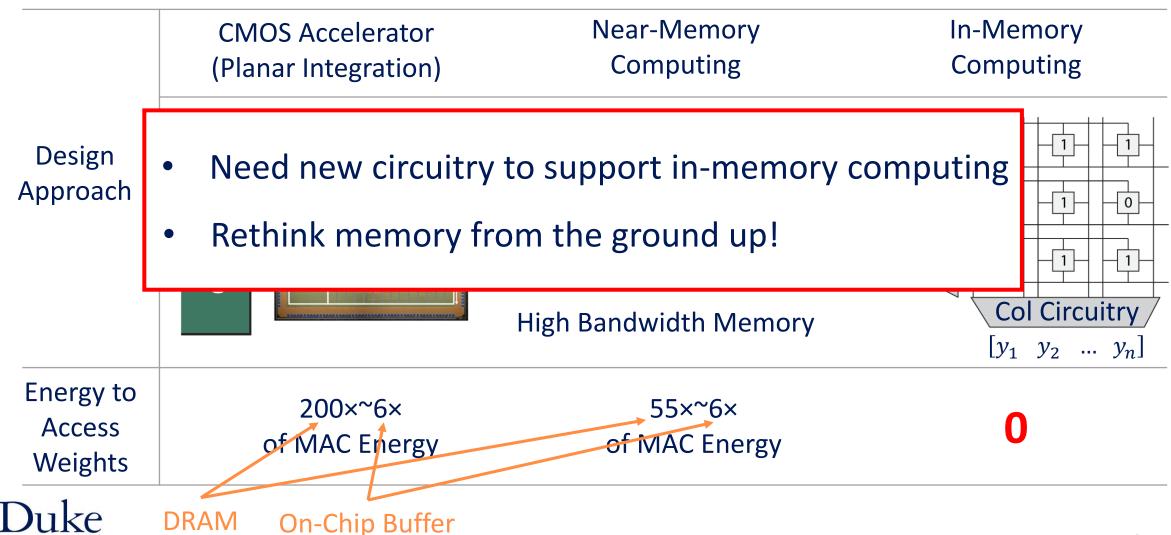




Uniqueness of Neural Network Execution

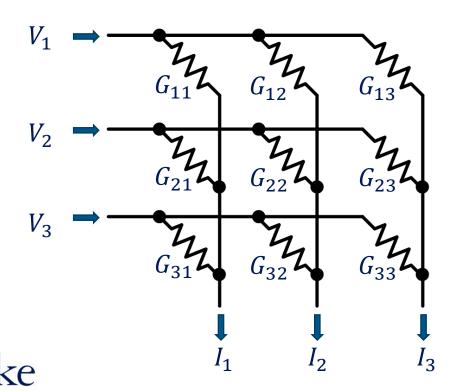


Make Memory Access Less Expensive



Key Idea of In-Memory Computing

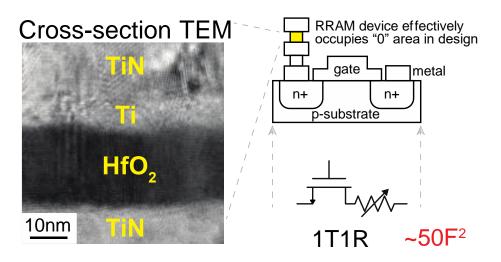
inputs weights
$$[V_1 \quad V_2 \quad V_3] \begin{bmatrix} G_{11} & G_{12} & G_{13} \\ G_{21} & G_{22} & G_{23} \\ G_{31} & G_{32} & G_{33} \end{bmatrix} = \begin{bmatrix} I_1 & I_2 & I_3 \end{bmatrix}$$

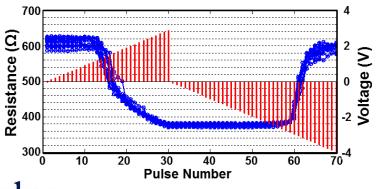


- Weight Matrix Stored as Conductance G
- Rely on Analog Computation (Kirchhoff's Current Law) for "almost free"
 - Multiplication: $I = V \cdot G$
 - Addition: $I^{column} = I_1^{row} + I_2^{row} + I_2^{row}$
- Ideal Nanoscale Devices for G:
 - Programmable Conductance
 - Multi-Level Cell
 - Small Footprint/High Density
 - Compatible with Existing CMOS Process

Memristors for In-Memory Computing

Also Called Resistive Random Access Memory, RRAM or ReRAM





Programmable resistor w/ analog states

ISSCC: Intel adds embedded ReRAM to 22nm portfolio

January 03, 2019

TSMC to start embedded RRAM production in 2019

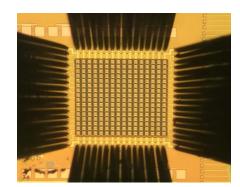
According to reports, Taiwan Semiconductor Manufacturing Company (TSMC) is aiming to start producing embedded RRAM chips in 2019 using a 22 nm process. This will be initial "risk production" to gauge market reception.

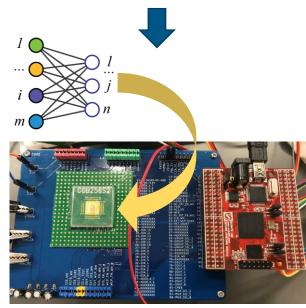
	Multi- Level Cell	Cell Area	R/W Speed
SRAM	×	large	Fast
DRAM	×	medium	Medium
1T1R	٧	medium	Medium Fast
Flash	٧	small	Slow



My work: Emerging Memory-Centric Design

- Circuits & Systems Implementation
 - Spike-based Interface [DAC'15, DAC'18, DAC'20]
 - Implementation of Neural Networks [VLSI'19, DAC'20]
- Tolerate/Exploit Non-ideal Behavior of Memristors
 - Device Nonlinearity [ISCAS'16, IEDM'17, IEDM'19]
 - Read Disturbance [ICCAD'17], Hard Fault [ITC'19]

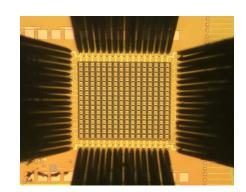


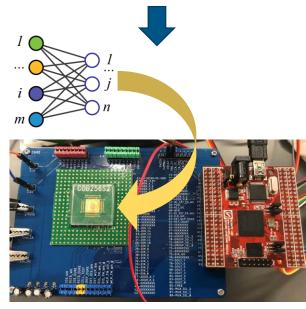




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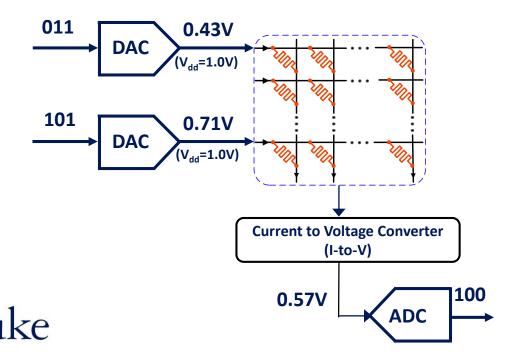




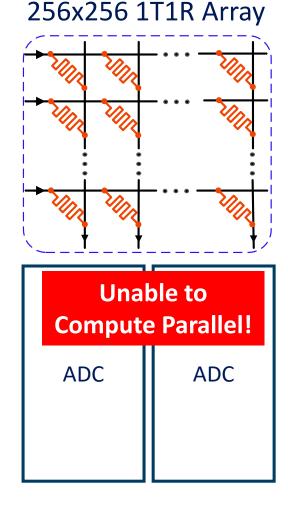
Conventional ADC is Too Large

The Level-based Design

- Compatible to existing signal processing
- High speed computation



Actual Layout:

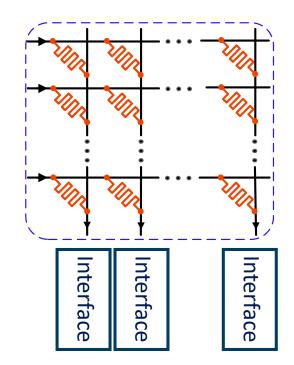


Based on 1.66MF² 8bit ADC by K. Ohhata (JSSC 2019)

My Approach: Spiking Interface Circuit

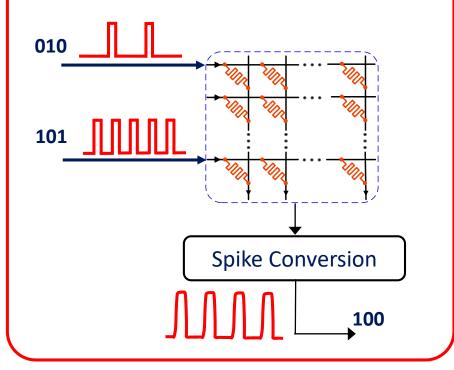
What Better Designs Look Like

- Compute Parallelly (Massive)
- Need Light-Weight Interface Circuitry



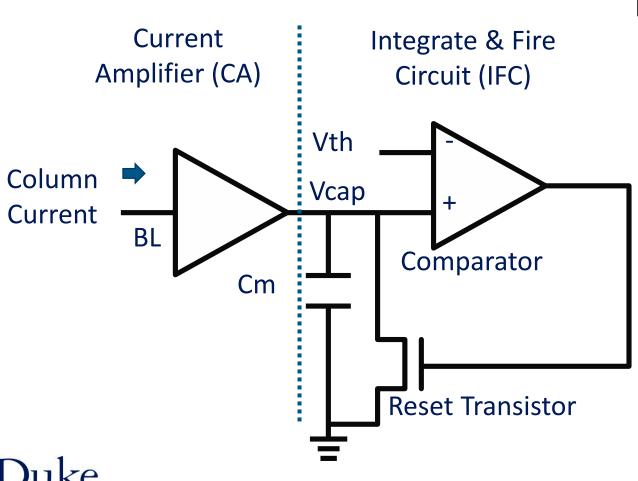
The Spike-based Design

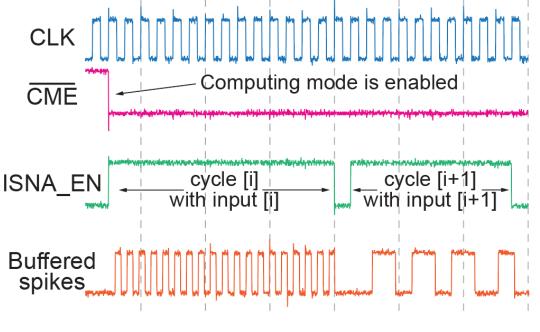
- Closer to biological system
- Extremely high power efficiency

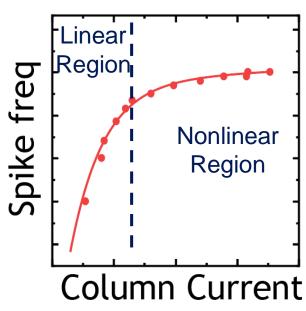




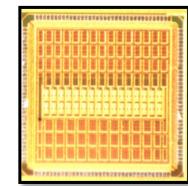
Spike Conversion



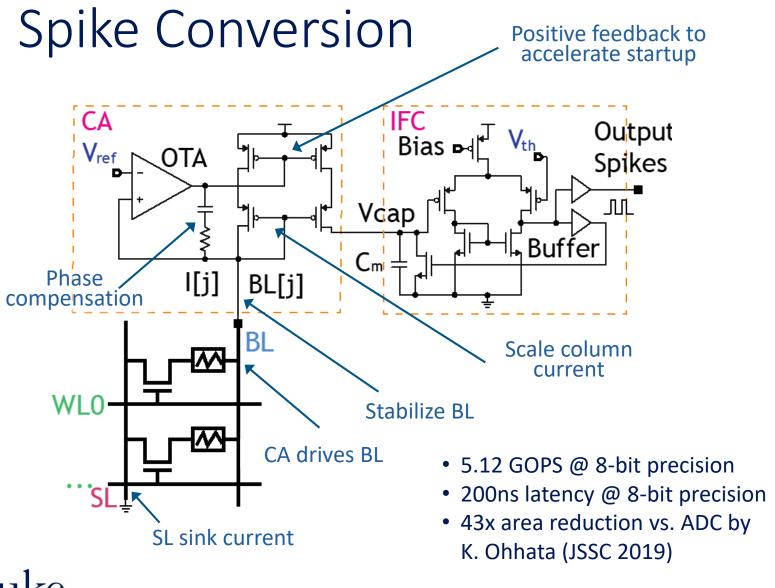


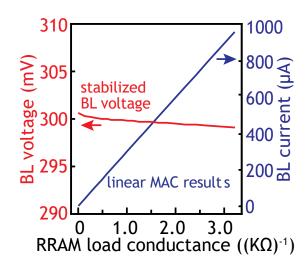


Spike Conversion Circuit & Controller 3152x3152 μm²

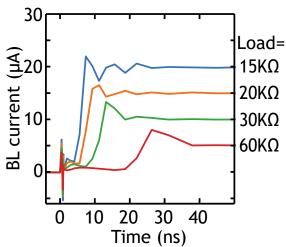


Duke





Tradeoff between large input current range and response speed



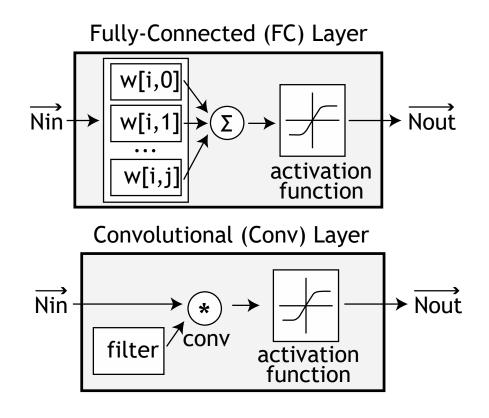
Enlarge phase margin tolerating capacitor positive feedback



How to Use Spiking-Based Design to Execute Neural Networks?



In Situ Nonlinear Activation (ISNA) Function

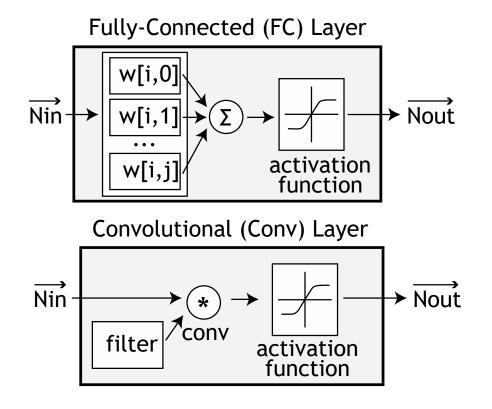


Single-layer Inference Operation:

- Step 1: Load data from buffer
- Step 2: Vector-matrix multiplication
- Step 3: Nonlinear activation function
- Step 4: Pooling
- Step 5: Store results to buffer
 - : digital domain (A): analog domain



In Situ Nonlinear Activation (ISNA) Function



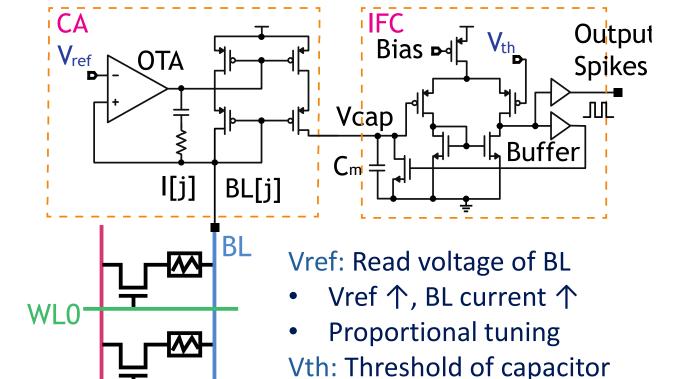
Single-layer Inference Operation:

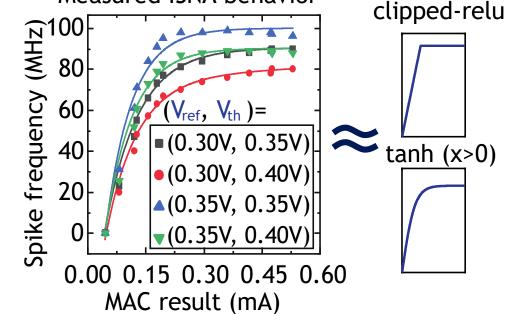
- Step 1: Load data from buffer
 - Step 2: Vector-matrix multiplication
 - Step 3: Nonlinear activation function
- Step 4: Pooling
- Step 5: Store results to buffer
 - : digital domain () : analog domain

Combine Step 2 & Step 3 to simplify PE operation: Use linear + nonlinear regions



Adjust Activation Function





Measured ISNA behavior

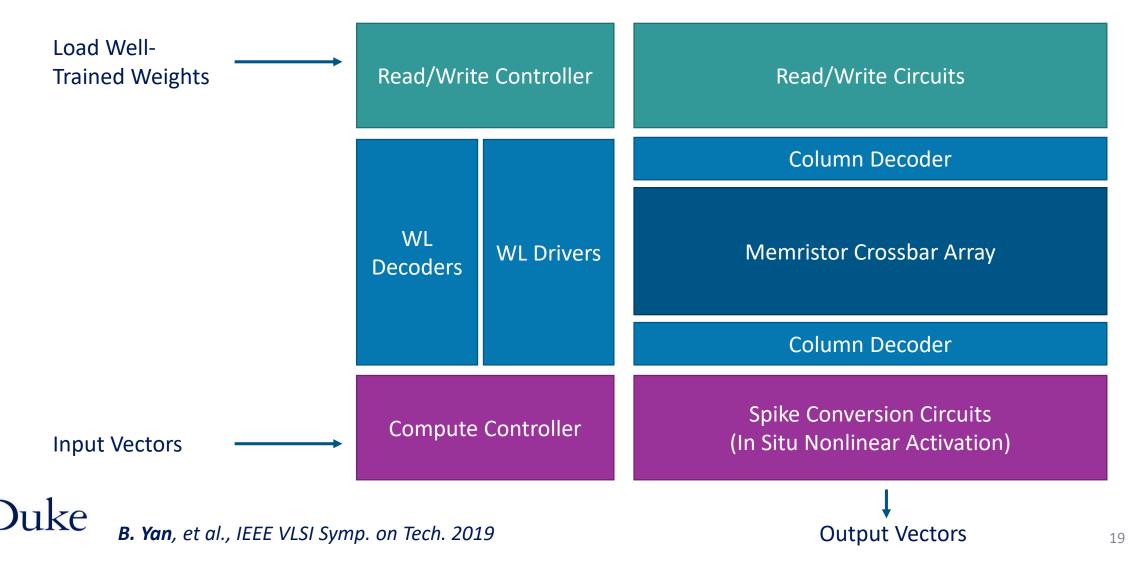
- Vth ↓, Charging/discharging ↑
- Distorted tuning

charging/discharging

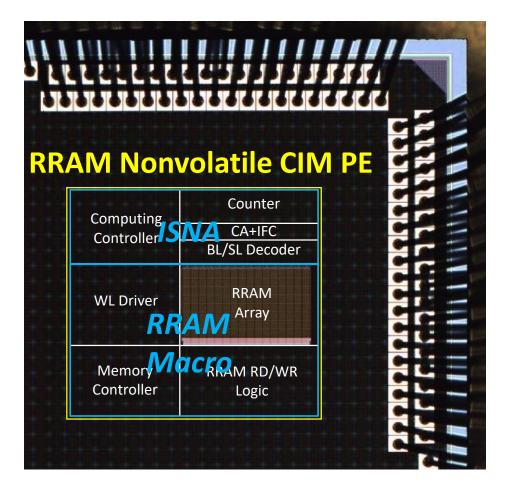


Function

Chip Architecture



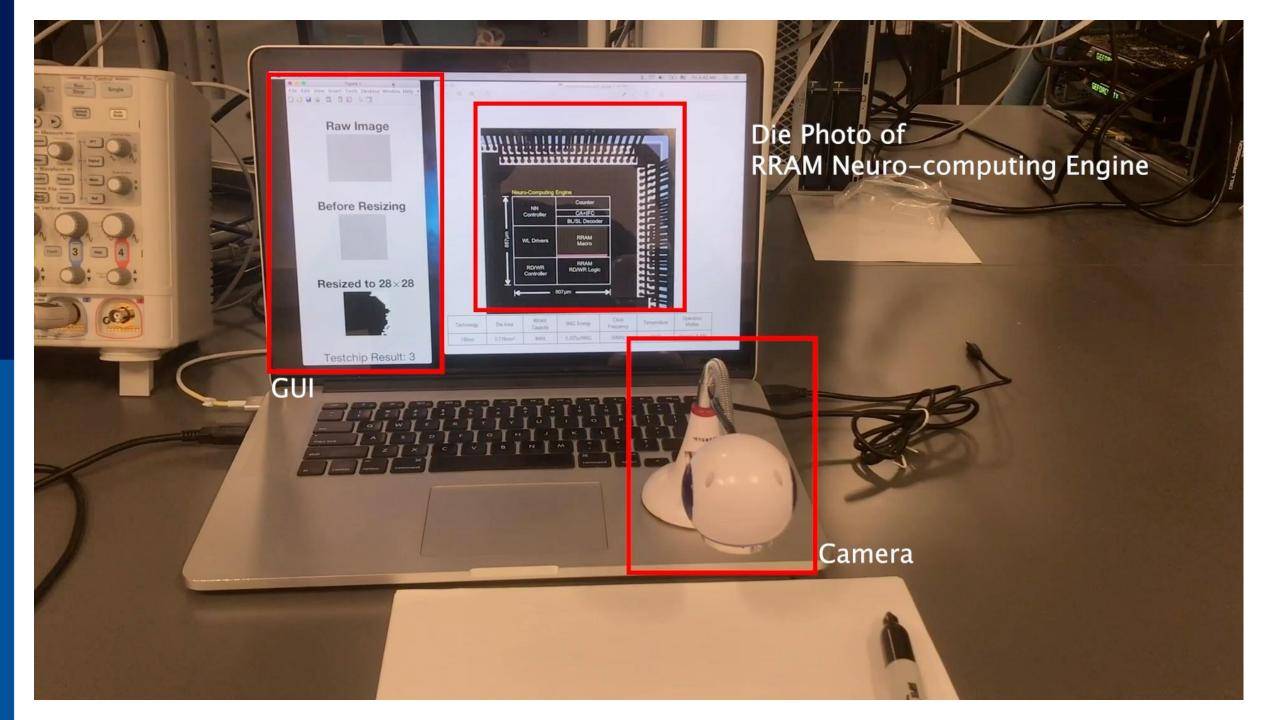
Chip Summary



Technology	150nm CMOS +HfO _x RRAM	
Macro Capacity	64K (256×256)	
Clock Frequency	50MHz	
Energy Efficiency	0.257pJ/Mac	
Average Power	1.52 mW	
Layer-wise Latency	200ns	
Real-time Benchmarks	3-layer perceptrons, LeNet-4, LetNet-5	



Demo video online: https://bit.ly/AICHIP



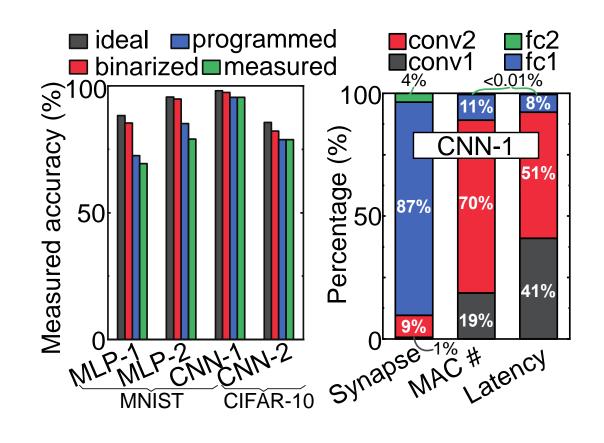
Evaluation: Measured Neural Network Results

MNIST:

- MLP-1: Single-layer perceptron
- MLP-2: 2-layer perceptron
- CNN-1: 4-Layer LeNet

CIFAR-10:

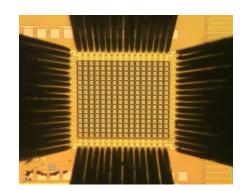
• CNN-2: 5-Layer LeNet

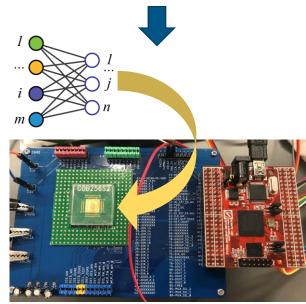




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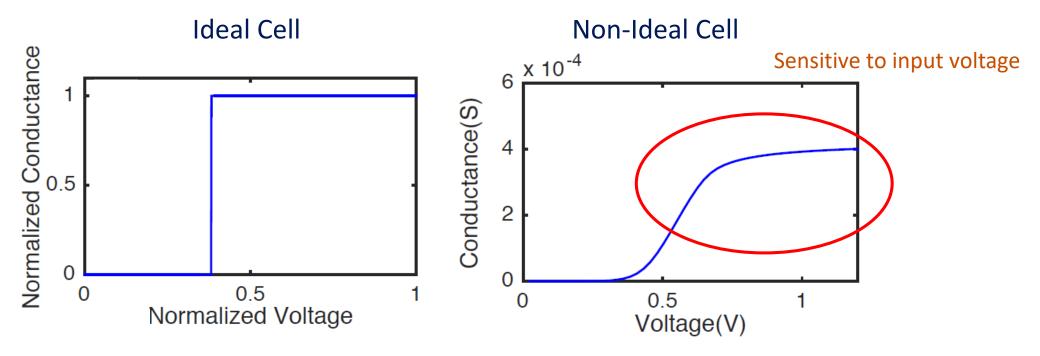






Non-Ideal Memristor - I

Cell Nonlinearity: conductance varies when applied with different voltages

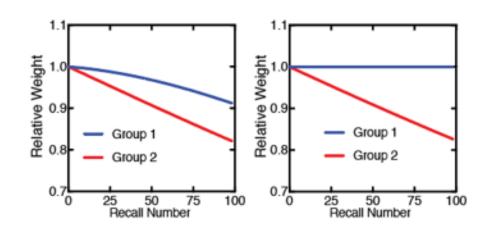


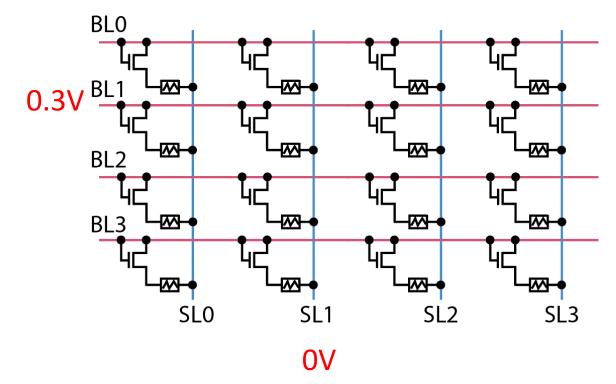
Solution: Current Amplifier to Clamp Cell Voltage (shown in previous circuit design part)



Non-Ideal Memristor - II

- Memristance Drift: conductance/memristance gradually deviates from original values under read voltage (read disturbance)
- Characteristic:
 - Very slow to observe







How to Mitigate Memristance Drift for Inference?

$$E_{mse} = \sum_{j}^{n} \left(t_{j} - \sum_{i}^{m} w_{ij} x_{i} \right)^{2} \qquad E'_{mse} = \sum_{j}^{n} \left(t_{j} - \sum_{i}^{m} w_{ij} x_{i} - \sum_{i}^{m} \Delta w_{ij} x_{i} \right)^{2} \qquad E_{\text{MSE}}: \text{MSE Error Function}$$

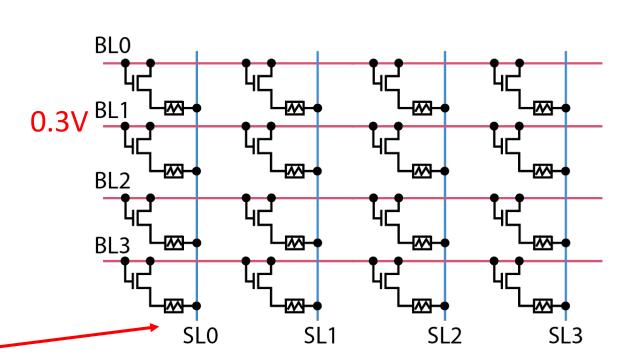
$$Voltage$$

$$\Delta E_{mse} = E'_{mse} - E_{mse}$$

$$= -2 \sum_{j}^{n} \left[\left(t_{j} - \sum_{i}^{m} w_{ij} x_{i} \right) \left(\sum_{i}^{m} \Delta w_{ij} x_{i} \right) \right]$$



$$\frac{\partial \Delta E_{mse}}{\partial \Delta w_{ij}} = -2\left(t_j - \sum_{i=1}^{m} w_{ij} x_i\right) x_i \le 0$$

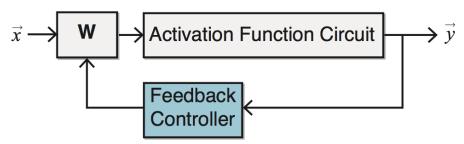


0V/0.6V

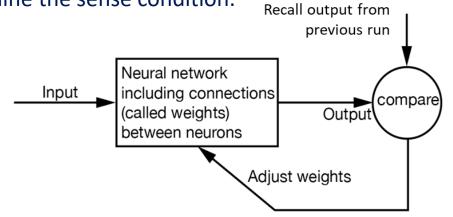
Change Column Current Direction

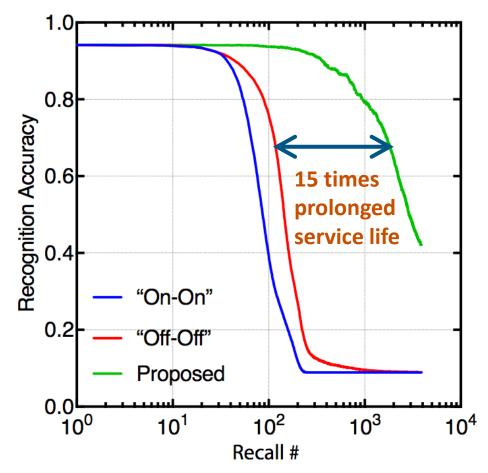
Closed-loop Design to Enhance Weight Stability

Feedback controller: Adjust the voltage condition to compensate the memristance drift.



"Arrogant principle": last output is used as the label to determine the sense condition.







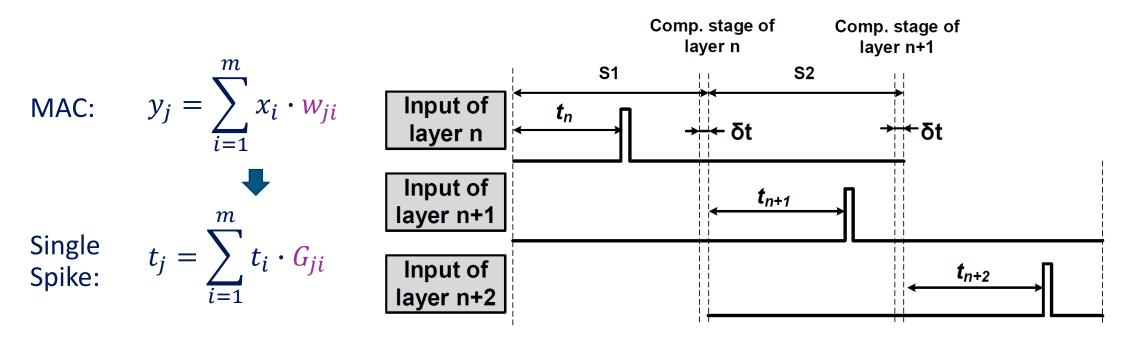
Summary

- The Past and Now of Al Hardware
 - In-Memory Computing Eliminates Weights Movement
- My Work:
 - Spiking-based In-Memory Computing Engine Offer Very High Energy Efficiency & Good Performance
 - Clever Design Methodologies (e.g., Closed-Loop Sensing) is Effective to Tolerate Nonideal Features of Memristors



Future Work I: Single Spike Processing Engine

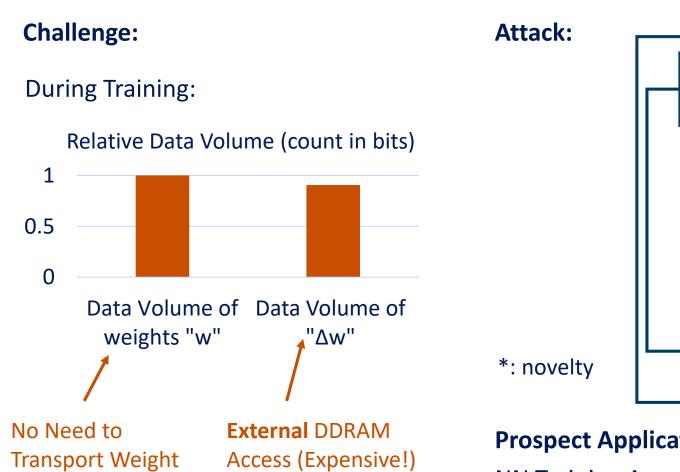
Use Single Spike to Replace Multiple Spikes: ~10x Improvement of Energy Efficiency

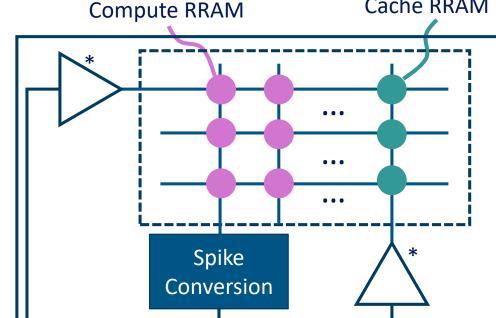


"ReSiPE: ReRAM-based Single-Spiking Processing-In-Memory Engine" Simulation Results Coming in July at Design Automation Conference (DAC) 2020



Future Work II: In-Memory Compute & Cache





Controller*

& Router

Prospect Applications:

NN Training Acceleration Self-Updatable In-Memory Computing Engine

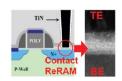
Cache RRAM

Long-Term Prospects

Compute

Control

Rethink Compute Memory Hierarchies







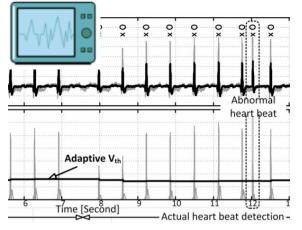
RRAM

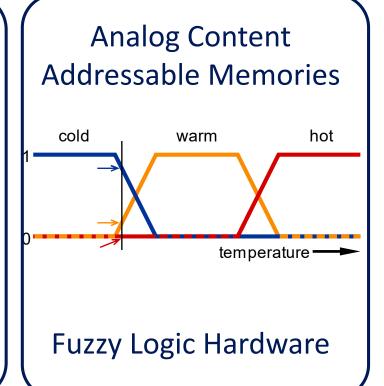
PCM

MRAM

"Organ" for Compute & Cache w/ different emerging memory types









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Prof. **Weisheng Zhao**Beihang University









Student Collaborators:

Ziru Li, Qilin Zheng, Brady Taylor









Thanks for Listening & Qs!

slides available at:

https://bonanyan.github.io/bn/

